

[0056] ABSTRACT OF THE DISCLOSURE

[0057] Disclosed is a method of forming a thick silicon oxide layer upon or internal to a silicon structure. The method is particularly useful in creating isolation regions within a silicon-containing structure, where such isolation regions can withstand high voltages. The electrically isolating thick silicon oxide layer or isolation regions can be shaped, machined, or etched to provide feedthroughs for vertical or horizontal interconnects. The feedthroughs may be coated with metal or filled with metal to provide the interconnect.

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